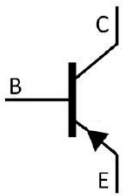


TO-92 PNP Silicon PNP transistor in a TO-92 Plastic Package.

2SC1213(A)
 Complementary pair with 2SC1213(A).

Low frequency power amplifier.

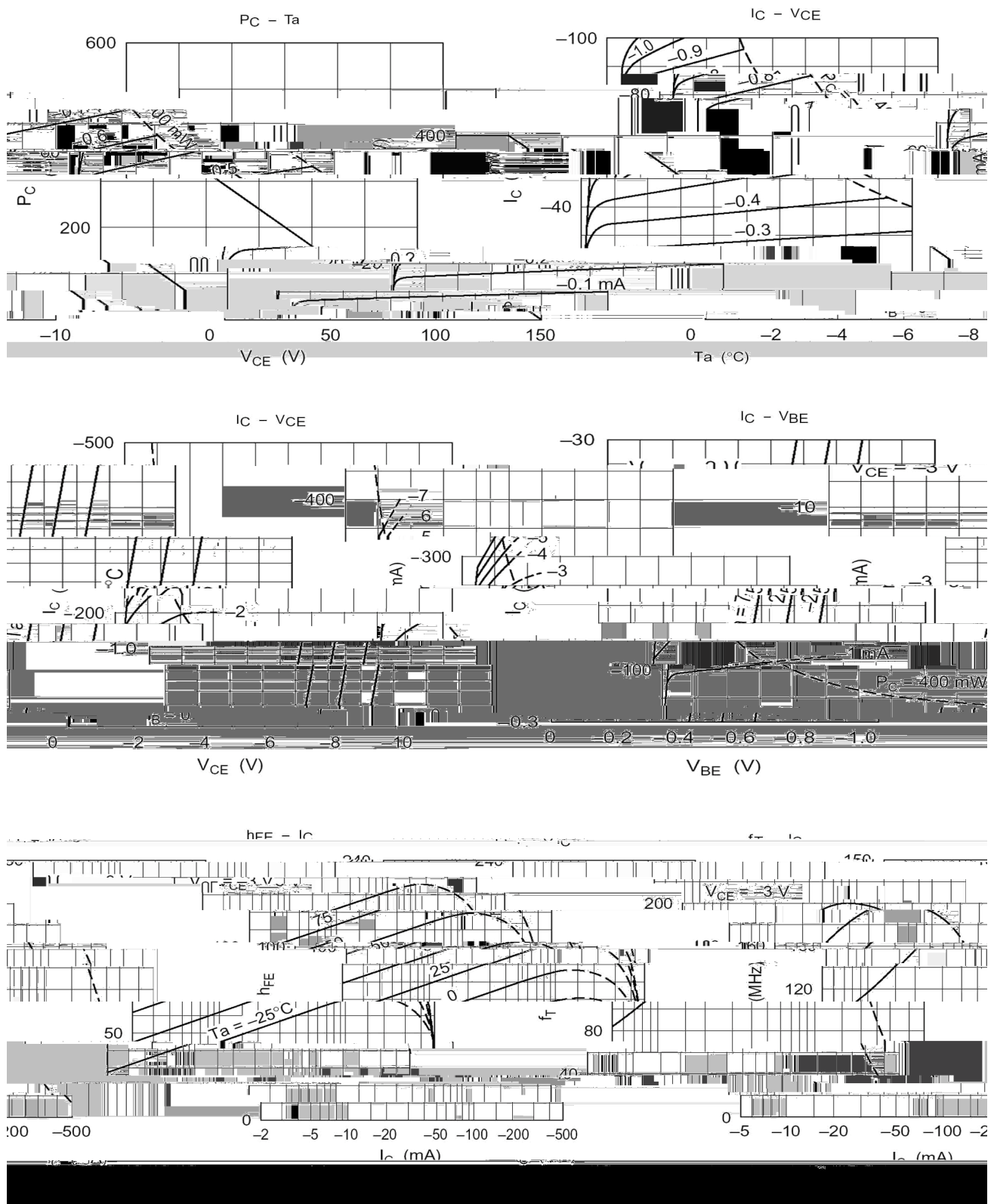


PIN1 Base PIN 2 Collector PIN 3 Emitter

h_{FE} Classifications Symbol	B	C	D
h_{FE} Range	60~120	100~200	160~320

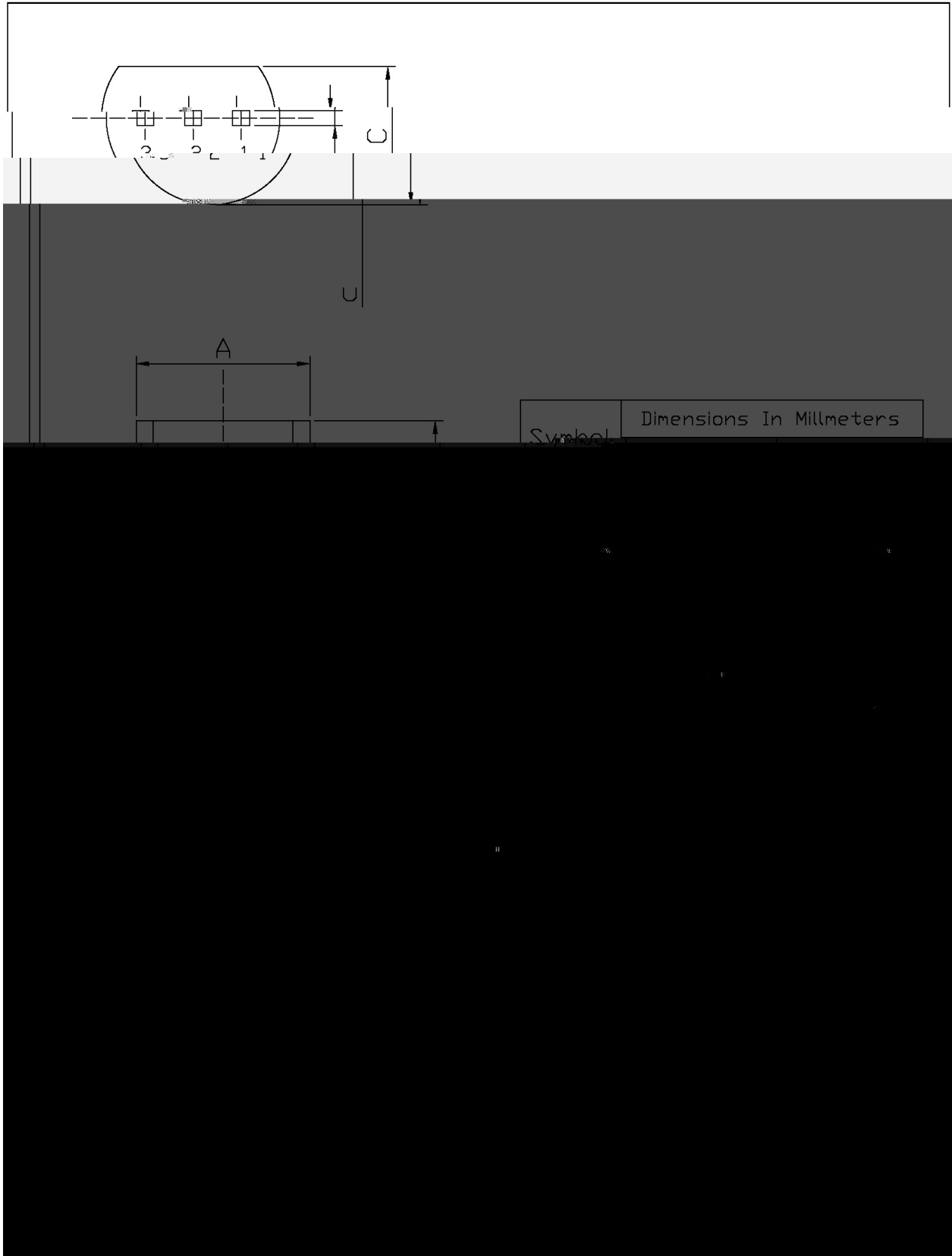
Parameter	Symbol		Rating	Unit
Collector to Base Voltage	V_{CBO}	2SA673	-35	V
		2SA673A	-50	
Collector to Emitter Voltage	V_{CEO}	2SA673	-35	V
		2SA673A	-50	
Emitter to Base Voltage	V_{EBO}		-4.0	V
Collector Current - Continuous	I_C		-500	mA
Collector Power Dissipation	P_C		400	mW
Junction Temperature	T_j		150	°C
Storage Temperature Range	T_{stg}		-55 150	°C

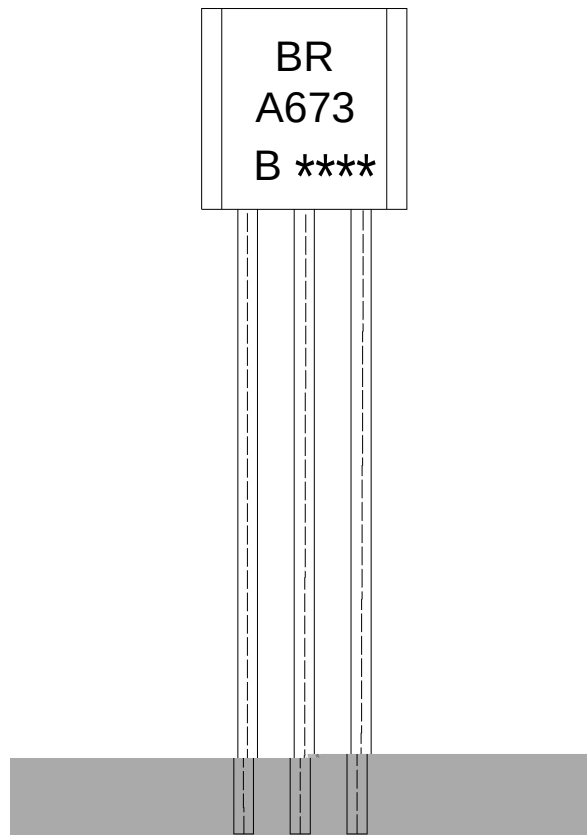
Parameter	Symbol		Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	2SA673	$I_C = -10\mu A$ $I_E = 0$	-35			V
		2SA673A		-50			
Collector to Emitter Breakdown Voltage	V_{CEO}	2SA673	$I_C = -1.0mA$ $I_B = 0$	-35			V
		2SA673A		-50			
Emitter to Base Breakdown Voltage	V_{EBO}		$I_E = -10\mu A$ $I_C = 0$	-4.0			V
Collector Cut-Off Current	I_{CBO}		$V_{CB} = -20V$ $I_E = 0$			-0.5	μA
DC Current Gain	$h_{FE(1)}$		$V_{CE} = -3.0V$ $I_C = -10mA$	60		320	
	$h_{FE(2)}$		$V_{CE} = -3.0V$ $I_C = -500mA$	10			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$		$I_C = -150mA$ $I_B = -15mA$		-0.2	-0.6	V
Base to Emitter Voltage	V_{BE}		$V_{CE} = -3.0V$ $I_C = -10mA$		-0.64		V



T0-92

Unit: mm





BR:

A673

B:

h_{FE}

Note:

BR:

Company Code.

A673:

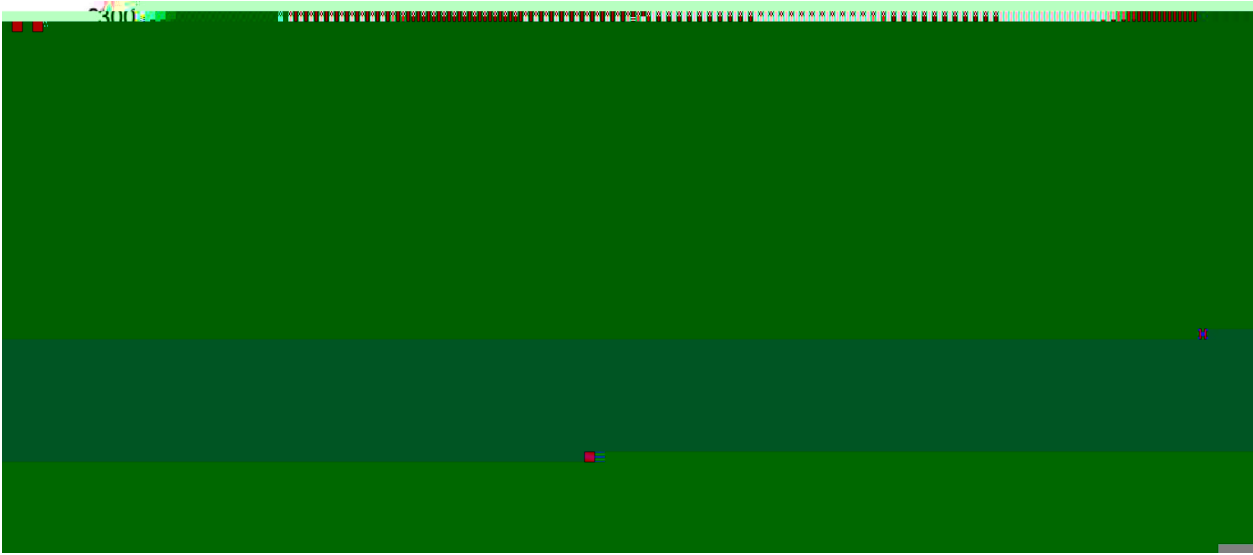
Product Type.

B:

h_{FE} Classifications Symbol

****:

Lot No. Code, code change with Lot No.



- 1

25 150

60 90sec;

2

255±5

5±0.5sec;

3

2 10

/sec.
- Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

270±5

10±1 sec.

Temp:270±5℃

Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱